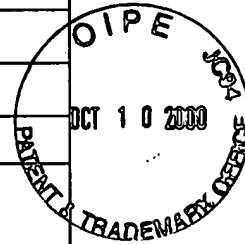


#2



INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: 150.00560102	Serial No.: 09/560,268
	Applicant(s): Whonchee Lee et al.	
	Filing Date: April 26, 2000	Group: 1746

## U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	SubClass	Filing Date If Appropriate
SL		4,528,066	07/09/85	Merkling et al.	438	696	
SL		5,010,032	04/23/91	Tang et al.	438	228	
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SL		5,880,033	03/09/99	Tsai	438	710	

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	SubClass	Translation	
							Yes	No
		NONE						

## OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

SL		Goto et al., "Optimization of Salicide Processes for sub 0.1-μm CMOS Devices", 1994 Symposium on VLSI Technology Digest of Technical Papers, pgs. 119-120 (1994).
SL		Ohguro et al., "Nitrogen-doped nickel monosilicide technique for deep submicron CMOS salicide", International Electron Devices Meeting, Washington, D.C., December 10-13, 1995, pgs. 10.3.1-10.3.4.

EXAMINER	SL	Date Considered	12/26/00
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.